A Sustainable and Precise Solution to IGZO Etch Residual Challenges Using Transient-Assisted Processing (TAP)

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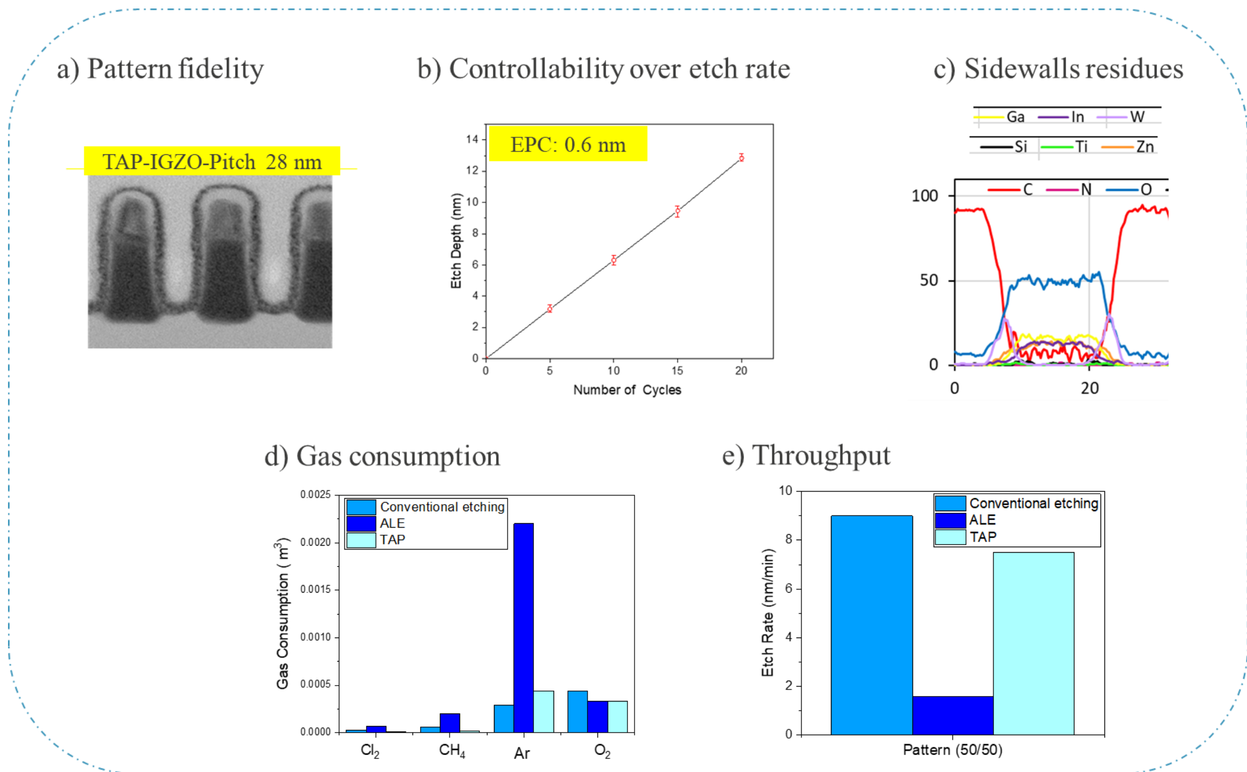

Figure 1. a) TEM of patterned IGZO at pitch 28nm, b) linear etch depth as a function of a number of cycles, c) EDX analysis demonstrating control over sidewall residues, d) Gas consumption comparison between ALE and TAP, and e) Etch rate comparison among conventional etching, ALE, and TAP for etching 30 nm of IGZO.

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